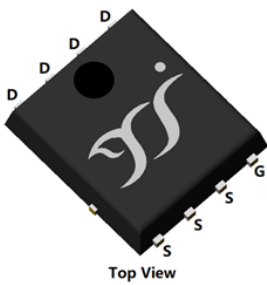
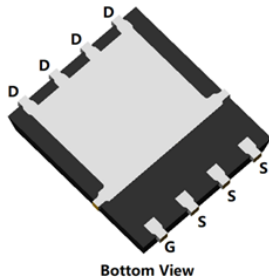


N-Channel Enhancement Mode Field Effect Transistor

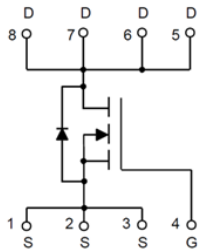


Top View



Bottom View

PDFN5060-8L



Product Summary

- V_{DS} 80V
- I_D 100A
- $R_{DS(ON)}$ (at $V_{GS}=10V$) < 4.5mohm
- 100% UIS Tested
- 100% ∇V_{DS} Tested

General Description

- Split gate trench MOSFET technology
- Excellent package for heat dissipation
- High density cell design for low $R_{DS(ON)}$

Applications

- Battery protection
- Load switch
- Uninterruptible power supply

■ Absolute Maximum Ratings ($T_A=25^\circ C$ unless otherwise noted)

Parameter		Symbol	Limit	Unit
Drain-source Voltage		V_{DS}	80	V
Gate-source Voltage		V_{GS}	± 20	V
Drain Current	$T_C=25^\circ C$	I_D	100	A
	$T_C=100^\circ C$		58	
Pulsed Drain Current ^A		I_{DM}	400	A
Avalanche energy ^B		E_{AS}	600	mJ
Total Power Dissipation ^C	$T_C=25^\circ C$	P_D	152	W
	$T_C=100^\circ C$		61	
Junction and Storage Temperature Range		T_J, T_{STG}	-55~+150	$^\circ C$

■ Thermal resistance

Parameter		Symbol	Limit	Units
Thermal Resistance Junction-to-Ambient ^D	$t \leq 10S$	$R_{\theta JA}$	22.3	$^\circ C/W$
Thermal Resistance Junction-to-Ambient ^D	Steady-State		40.7	
Thermal Resistance Junction-to-Case	Steady-State	$R_{\theta JC}$	0.819	

■ Ordering Information (Example)

PREFERRED P/N	PACKING CODE	Marking	MINIMUM PACKAGE(pcs)	INNER BOX QUANTITY(pcs)	OUTER CARTON QUANTITY(pcs)	DELIVERY MODE
YJG100G08A	F1	YJG100G08A	5000	10000	100000	13" reel



YJG100G08A

■ Electrical Characteristics (T_J=25°C unless otherwise noted)

Parameter	Symbol	Conditions	Min	Typ	Max	Units
Static Parameter						
Drain-Source Breakdown Voltage	BV _{DSS}	V _{GS} =0V, I _D =250μA	80	-	-	V
Zero Gate Voltage Drain Current	I _{DSS}	V _{DS} =80V, V _{GS} =0V	-	-	1	μA
Gate-Body Leakage Current	I _{GSS}	V _{GS} = ±20V, V _{DS} =0V	-	-	±100	nA
Gate Threshold Voltage	V _{GS(th)}	V _{DS} = V _{GS} , I _D =250μA	2.0	3.0	4.0	V
Static Drain-Source On-Resistance	R _{DS(on)}	V _{GS} =10V, I _D =20A	-	3.6	4.5	mΩ
Diode Forward Voltage	V _{SD}	I _S =20A, V _{GS} =0V	-	0.8	1.2	V
Maximum Body-Diode Continuous Current	I _S		-	-	100	A
Gate resistance	R _G	f=1MHz, Open drain	-	2	-	Ω
Transconductance	G _{fs}	V _{DS} =10V, I _D =50A		71.5		S
Dynamic Parameters						
Input Capacitance	C _{iss}	V _{DS} =40V, V _{GS} =0V, f=1MHz	-	5666	-	pF
Output Capacitance	C _{oss}		-	860	-	
Reverse Transfer Capacitance	C _{rss}		-	7.5	-	
Switching Parameters						
Total Gate Charge	Q _g	V _{DS} =40V, V _{GS} =10V, I _D =50A	-	73	-	nC
Gate-Source Charge	Q _{gs}		-	25	-	
Gate-Drain Charge	Q _{gd}		-	12	-	
Reverse Recovery Charge	Q _{rr}	I _F =50A, di/dt=100A/us	-	50	-	
Reverse Recovery Time	t _{rr}		-	44	-	
Turn-on Delay Time	t _{D(on)}	V _{DS} =40V, V _{GS} =10V, R _G =3Ω, I _D =50A	-	27	-	ns
Turn-on Rise Time	t _r		-	32	-	
Turn-off Delay Time	t _{D(off)}		-	54	-	
Turn-off fall Time	t _f		-	17	-	

A. Repetitive rating; pulse width limited by max. junction temperature.

B. T_J=25°C, V_{DD}=50V, V_{GS}=10V, L=3mH I_{as}=20A.

C. P_d is based on max. junction temperature, using junction-case thermal resistance.

D. The value of R_{θJA} is measured with the device mounted on 1in2 FR-4 board with 2oz. Copper, in a still air environment with T_A=25° C.



■ Typical Performance Characteristics

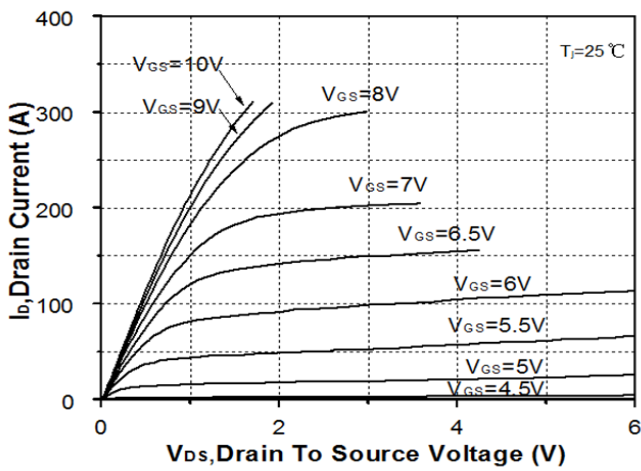


Figure1. Output Characteristics

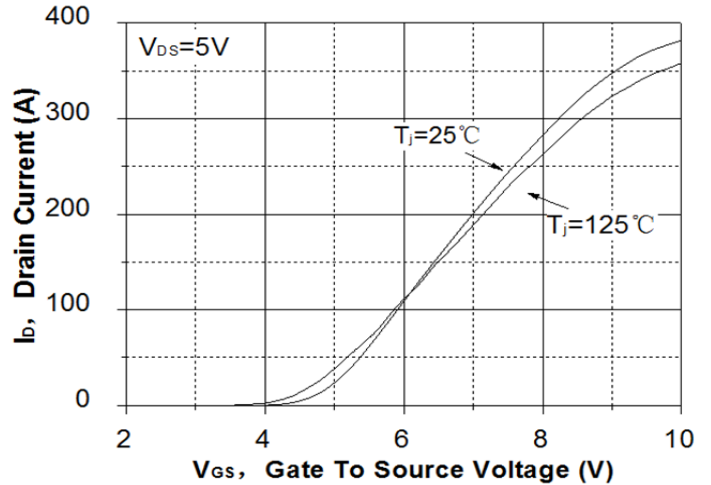


Figure2. Transfer Characteristics

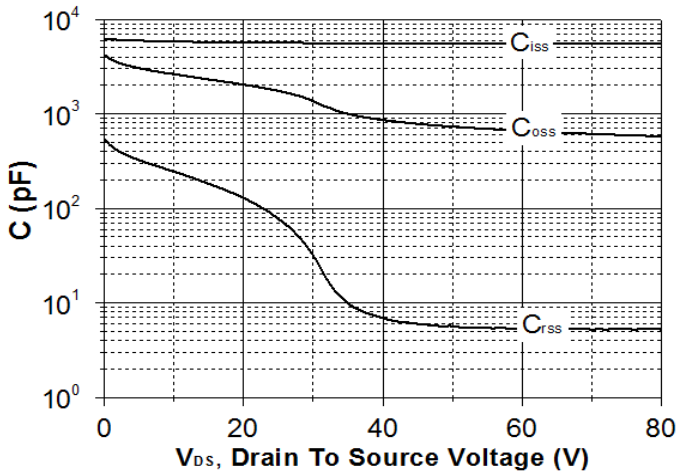


Figure3. Capacitance Characteristics

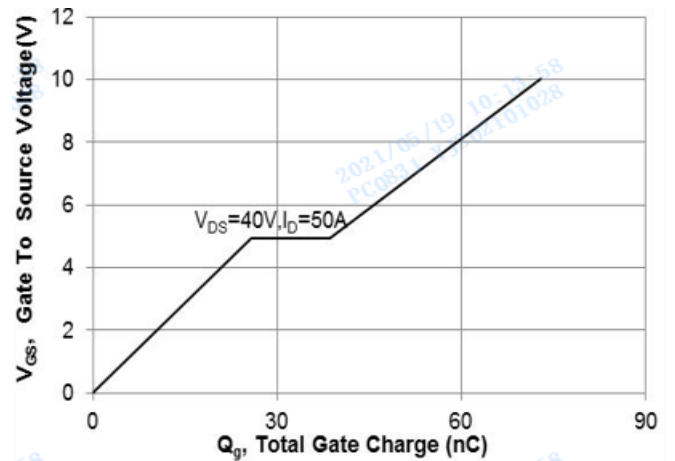


Figure4. Gate Charge

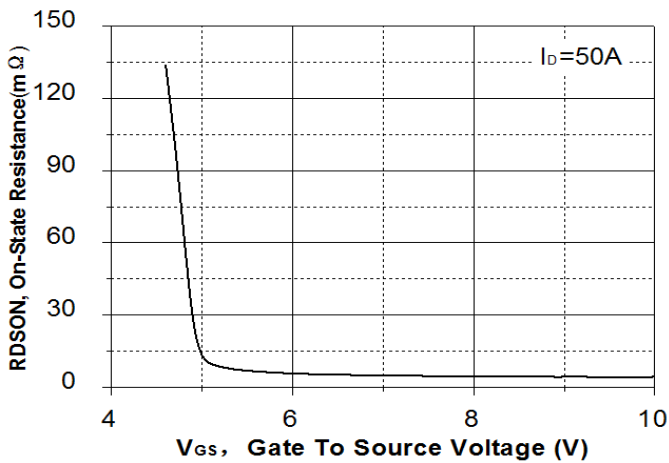


Figure5. On-Resistance vs. Gate to Source Voltage

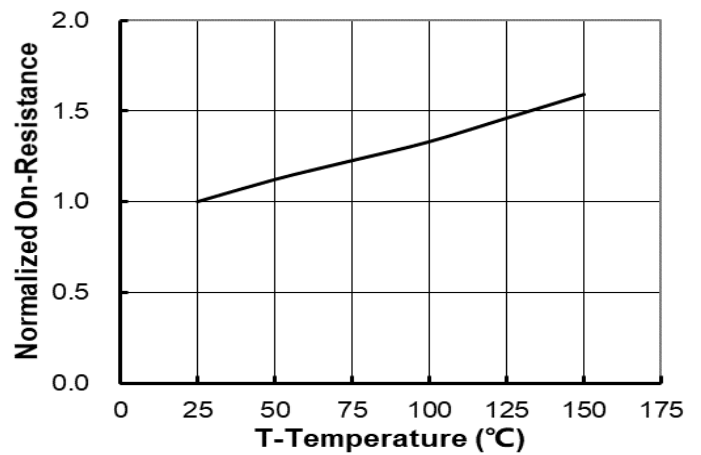


Figure6. Normalized On-Resistance



YJG100G08A

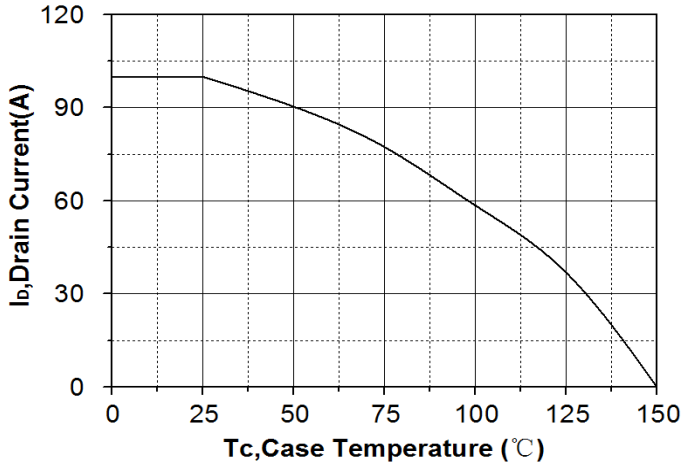


Figure7. Drain current

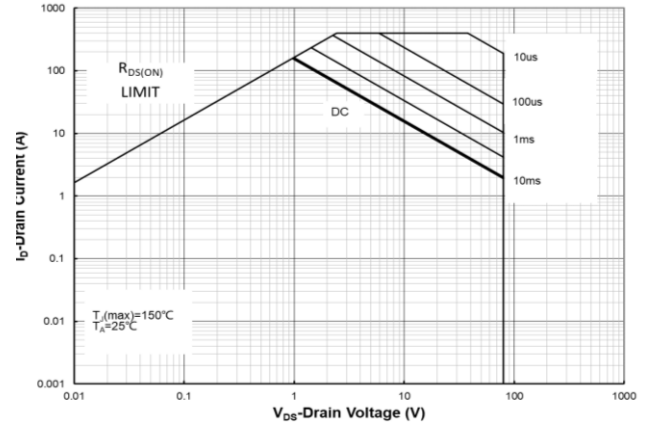


Figure8. Safe Operation Area

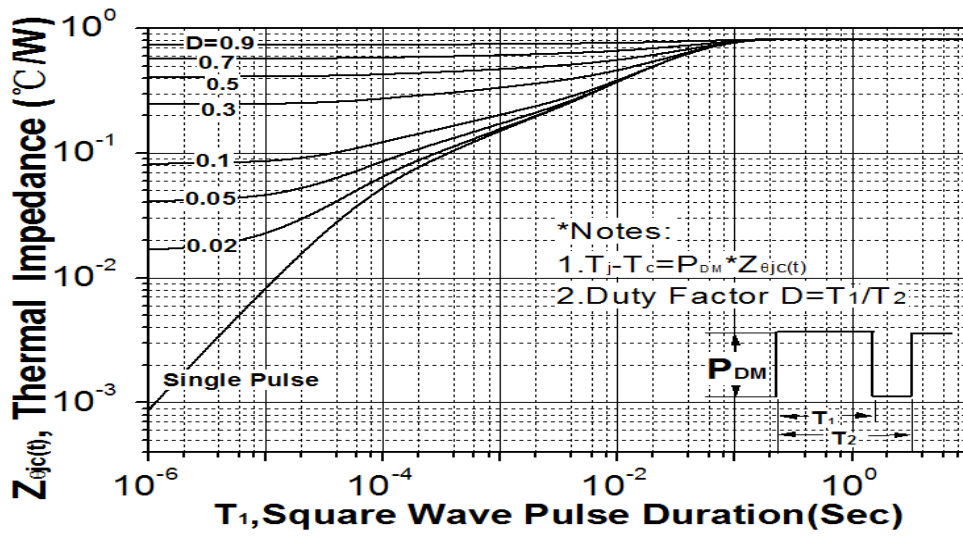
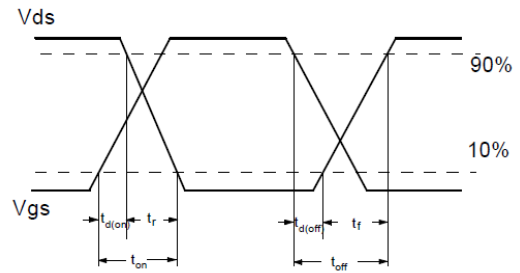
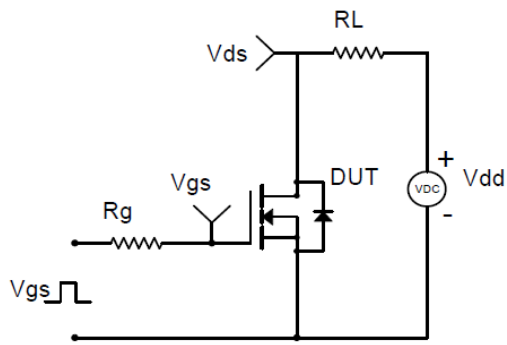
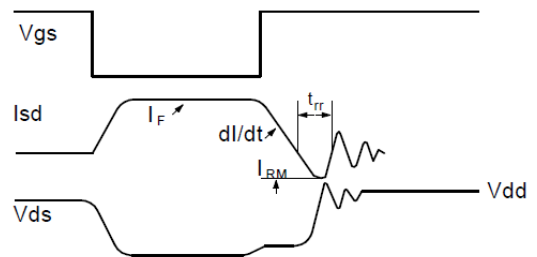
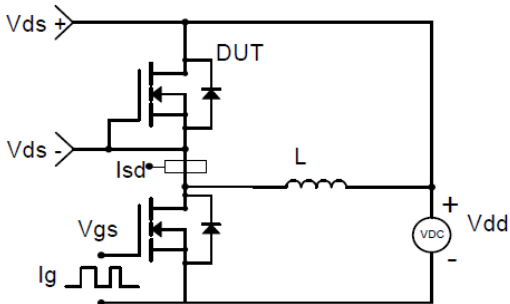


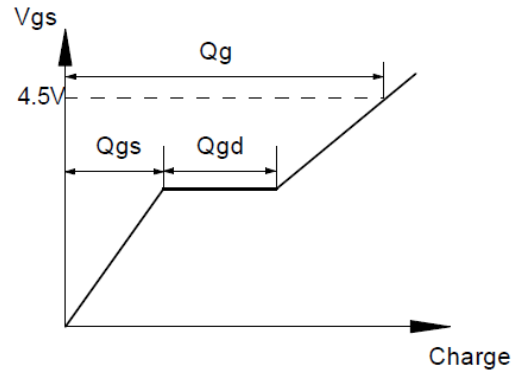
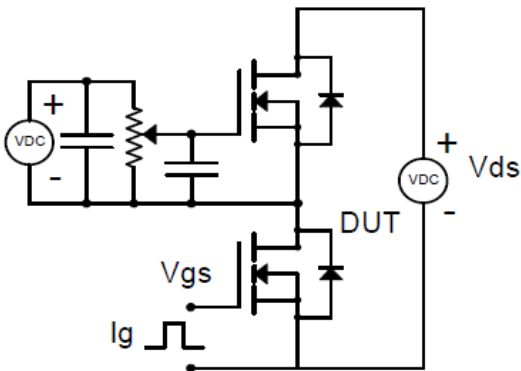
Figure9. Normalized Maximum Transient thermal impedance



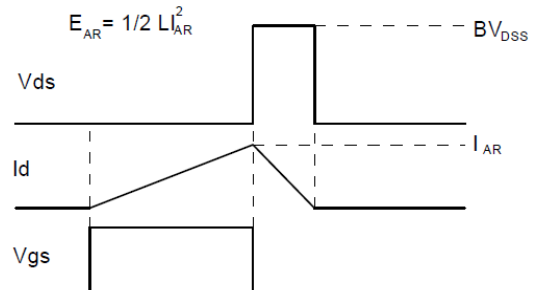
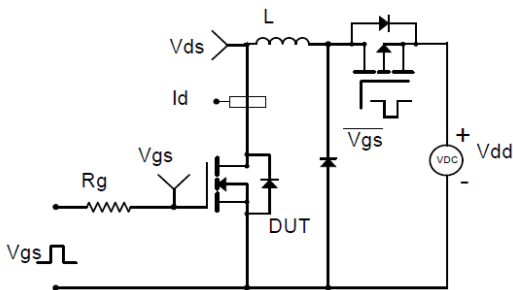
Resistive Switching Test Circuit & Waveforms



Diode Recovery Test Circuit & Waveforms



Gate Charge Test Circuit & Waveform

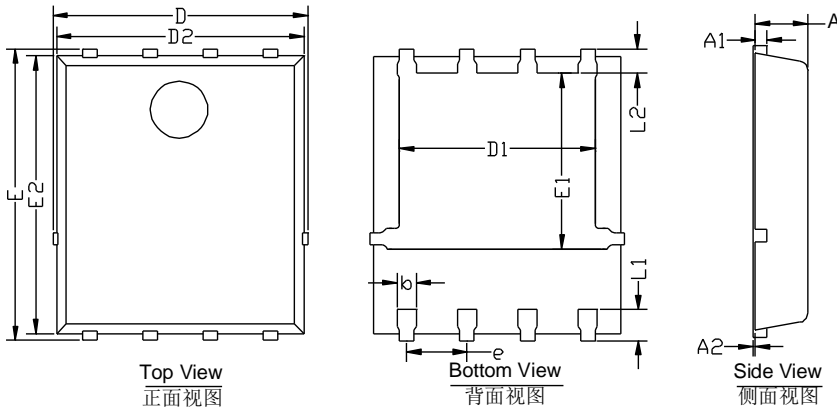


Unclamped Inductive Switching (UIS) Test Circuit & Waveforms

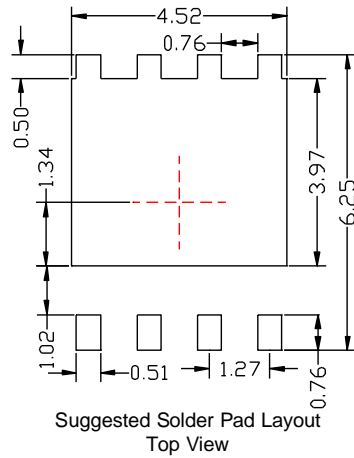


YJG100G08A

■ PDFN5060-8L Package information



SYMBOL	MILLIMETER		
	MIN	NOM	MAX
D	5.15	5.35	5.55
E	5.95	6.15	6.35
A	1.00	1.10	1.20
A1	0.254 BSC		
A2			0.10
D1	3.92	4.12	4.32
E1	3.52	3.72	3.92
D2	5.00	5.20	5.40
E2	5.66	5.86	6.06
L1	0.56	0.66	0.76
L2	0.50 BSC		
b	0.31	0.41	0.51
e	1.27 BSC		



Note:
 1. Controlling dimension: in millimeters.
 2. General tolerance: $\pm 0.10\text{mm}$.
 3. The pad layout is for reference purposes only.



YJG100G08A

Disclaimer

The information presented in this document is for reference only. Yangzhou Yangjie Electronic Technology Co., Ltd. reserves the right to make changes without notice for the specification of the products displayed herein to improve reliability, function or design or otherwise.

The product listed herein is designed to be used with ordinary electronic equipment or devices, and not designed to be used with equipment or devices which require high level of reliability and the malfunction of which would directly endanger human life (such as medical instruments, transportation equipment, aerospace machinery, nuclear-reactor controllers, fuel controllers and other safety devices), Yangjie or anyone on its behalf, assumes no responsibility or liability for any damages resulting from such improper use of sale.

This publication supersedes & replaces all information previously supplied. For additional information, please visit our website <http://www.21yangjie.com> , or consult your nearest Yangjie's sales office for further assistance.